Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	759	257/412.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/23 14:15
L2	0	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and ((gate with (platinum pt rhodium rh ruthenium ru iridium ir osmium os)) same ((plug interconnect wiring trace via contact) with (copper cu)) same (source drain))	US-PGPUB; USPAT	OR	ON	2005/07/23 14:32
L3	17	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and (polysilicon with gate with (platinum pt rhodium rh ruthenium ru iridium ir osmium os))	US-PGPUB; USPAT	OR	ON	2005/07/23 14:33
L4	25	((gate with (platinum pt rhodium rh ruthenium ru iridium ir osmium os)) same ((plug interconnect wiring trace via contact) with (copper cu)) same (source drain))	US-PGPUB; USPAT	OR	ON	2005/07/23 14:36
L5	48	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and (gate same ((plug interconnect wiring trace via contact) with (copper cu)) same (source drain))	US-PGPUB; USPAT	OR	ON	2005/07/23 14:41
L6	23	(gate with ((plug contact) near2 (copper cu)) with (source drain))	US-PGPUB; USPAT	OR	ON	2005/07/23 14:47
L7	34	438/620.ccls. and ((plug contact) with (copper cu))	US-PGPUB; USPAT	OR	ON	2005/07/23 14:50
L8	1	((insulat$4 dielectric oxide dioxide nitride interlayer) with (silicon si)) and ((unit adj cell) (lattice near4 (constant mismatch$4 match$4))) and ((atom$2 near (radius radii)) (bond$4 near energy))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 14:53
L9	40	((atom$2 near (radius radii)) (bond$4 near energy)) and (semiconductor silicon si wafer substrate) and (copper cu) and (rhodium rh ruthenium ru iridium ir osmium os platinum pt)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 14:53

L10	9	(semiconductor silicon si wafer substrate) and ((interconnect$5 metal$1is$7 metal$1iz$7) same ((platinum pt) near4 (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer")) same ((osmium os) with (palladium pd cobalt co nickel ni titanium ti) with (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer")))	US-PGPUB; USPAT	OR	ON	2005/07/23 14:56
L11	331	((atom$2 near (radius radii)) (bond$4 near energy)) and (semiconductor silicon si wafer substrate) and ((copper cu) same (rhodium rh ruthenium ru iridium ir osmium os platinum pt) same (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer"))	US-PGPUB; USPAT	OR	ON	2005/07/23 14:58
L12	151	((insulat$4 dielectric oxide dioxide nitride interlayer) with (silicon si)) and ((unit adj cell) (lattice near4 (constant mismatch$4 match$4)) (atom$2 near (radius radii)) (bond$4 near energy)) and ((film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer") with (conduct$5 platinum pt copper cu silver ag gold au rhodium rh ruthenium ru iridium ir osmium os palladium pd cobalt co nickel ni titanium ti))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 15:11
L13	277	(semiconductor silicon si wafer substrate) and ((insulat$4 dielectric oxide dioxide nitride interlayer) with (silicon si)) and ((unit adj cell) (lattice near4 (constant mismatch$4 match$4))) and ((atom$2 near (radius radii)) (bond$4 near energy))	US-PGPUB; USPAT	OR	ON	2005/07/23 15:13

L14	459	(semiconductor silicon si wafer substrate) and ((interconnect$5 metal$1is$7 metal$1iz$7) same ((copper cu silver ag gold au) near4 (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer")) same ((rhodium rh ruthenium ru iridium ir osmium os platinum pt) with (palladium pd cobalt co nickel ni titanium ti) with (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer") with (element constituent consist$3 compris$3 atom metal)))	US-PGPUB; USPAT	OR	ON	2005/07/23 15:21
L15	18693	(gate with (platinum pt ruthenium ru iridium ir osmium os))	US-PGPUB; USPAT	OR	ON	2005/07/23 15:32
L16	152	L15 and (257/412.ccls. 257/413. ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls. 438/620.ccls.)	US-PGPUB; USPAT	OR	ON	2005/07/23 15:32
L17	10332	(gate with (platinum pt ruthenium ru iridium ir osmium os))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 15:55
L18	90	L17 and (copper cu)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 15:55
L19	72	L15 same ((plug interconnect$8 wiri$6 trace via contact line) with (copper cu))	US-PGPUB; USPAT	OR	ON	2005/07/23 16:03
L20	3693	((platinum pt rhodium rh ruthenium ru iridium ir osmium os) same (copper cu) same (palladium pd titanium ti cobalt co nickel ni)). clm.	US-PGPUB	OR	ON	2005/07/23 16:08
L21	0	((platinum pt rhodium rh ruthenium ru iridium ir osmium os) same (copper cu) same (palladium pd titanium ti cobalt co nickel ni) same gate same (plug via contact)).clm.	US-PGPUB	OR	ON	2005/07/23 16:11
L22	180	((platinum pt rhodium rh ruthenium ru iridium ir osmium os) same (copper cu) same (palladium pd titanium ti cobalt co nickel ni) same (gate plug via contact)).clm.	US-PGPUB	OR	ON	2005/07/23 16:11
L23	28	((platinum pt rhodium rh ruthenium ru iridium ir osmium os) same (copper cu) same (palladium pd titanium ti cobalt co nickel ni) same gate).clm.	US-PGPUB	OR	ON	2005/07/23 16:13

L24	14	((ruthenium ru iridium ir osmium os) same (copper cu) same gate). clm.	US-PGPUB	OR	ON	2005/07/23 16:24